



MBR8045 thru MBR80100R

Silicon Power Schottky Diode

$V_{RRM} = 20\text{ V} - 100\text{ V}$

$I_F = 80\text{ A}$

Features

- High Surge Capability
- Types up to 100 V V_{RRM}

DO-5 Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR8045 (R)	MBR8060 (R)	MBR8080 (R)	MBR80100 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		45	60	80	100	V
RMS reverse voltage	V_{RMS}		32	42	50	70	V
DC blocking voltage	V_{DC}		45	60	80	100	V
Continuous forward current	I_F	$T_C \leq 120\text{ °C}$	80	80	80	80	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	1000	1000	1000	1000	A
Operating temperature	T_j		-65 to 150	-65 to 150	-65 to 150	-65 to 150	°C
Storage temperature	T_{stg}		-65 to 175	-65 to 175	-65 to 175	-65 to 175	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBR8045 (R)	MBR8060(R)	MBR8080 (R)	MBR80100 (R)	Unit
Diode forward voltage	V_F	$I_F = 80\text{ A}$, $T_j = 25\text{ °C}$	0.65	0.75	0.84	0.84	V
Reverse current	I_R	$V_R = 20\text{ V}$, $T_j = 25\text{ °C}$	5	5	5	5	mA
		$V_R = 20\text{ V}$, $T_j = 125\text{ °C}$	250	250	250	250	

Thermal characteristics

Parameter	Symbol	Conditions	MBR8045 (R)	MBR8060 (R)	MBR8080 (R)	MBR80100 (R)	Unit
Thermal resistance, junction - case	R_{thJC}		1.0	1.0	1.0	1.0	°C/W

